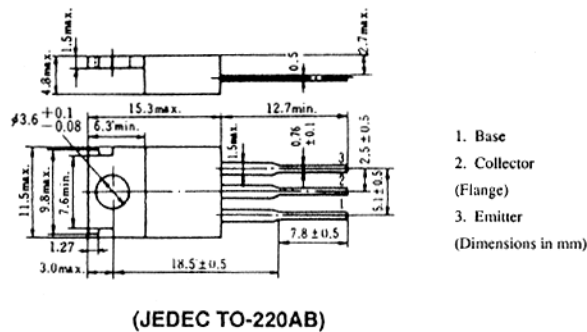


2SB861

SILICON PNP TRIPLE DIFFUSED
LOW FREQUENCY POWER AMPLIFIER
COLOR TV VERTICAL DEFLECTION OUTPUT
COMPLEMENTARY PAIR WITH 2SD1138

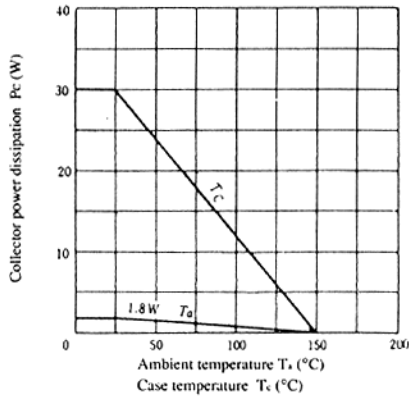


■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SB861	Unit
Collector to base voltage	VCBO	-200	V
Collector to emitter voltage	VCEO	-150	V
Emitter to base voltage	VEBO	-6	V
Collector current	IC	-2	A
Collector peak current	ic(peak)	-5	A
Collector power dissipation	PC	1.8	W
	PC*	30	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-45 to +150	°C

* Value at Tc = 25°C

MAXIMUM COLLECTOR DISSIPATION
CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

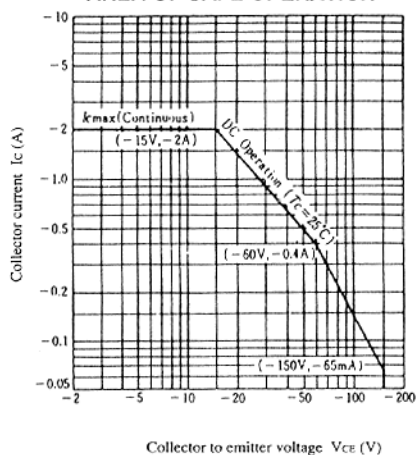
Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to emitter breakdown voltage	V(BR)CEO	IC = -50mA, RBE = ∞	-150	—	—	V
Emitter to base breakdown voltage	V(BR)EBO	IE = -5mA, IC = 0	-6	—	—	V
Collector cutoff current	ICBO	VCB = -120V, IE = 0	—	—	-1	μA
DC current transfer ratio	hFE1*	VCE = -4V, IC = -50mA	60	—	200	
	hFE2	VCE = -10V, IC = -500mA**	60	—	—	
Collector to emitter saturation voltage	VCE(sat)	IC = -500mA, IB = -50mA	—	—	-3	V
Base to emitter voltage	VBE	VCE = -4V, IC = -50mA	—	—	-1	V
Collector output capacitance	Cob	VCB = -100V, IE = 0, f = 1MHz	—	30	—	pF

* The 2SB861 is grouped by hFE1 as follows.

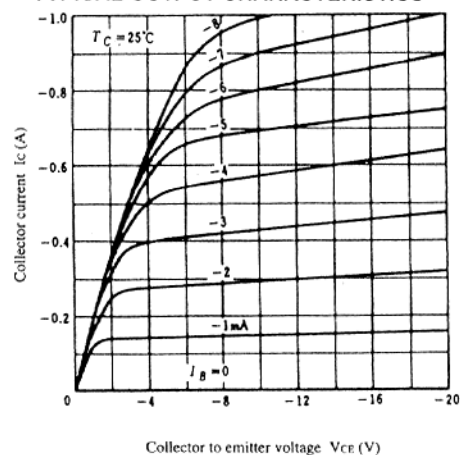
** Pulse Test

B	C
60 to 120	100 to 200

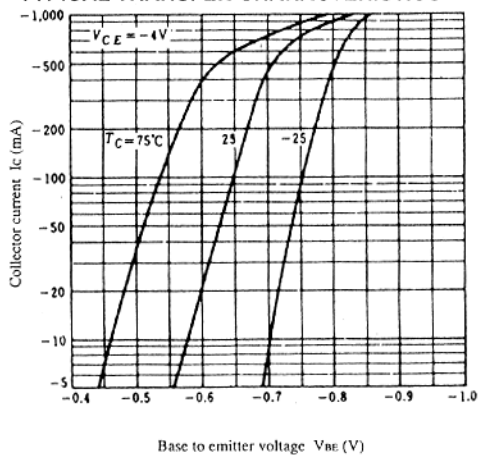
AREA OF SAFE OPERATION



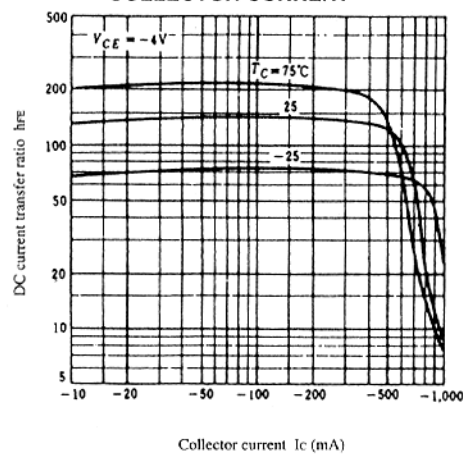
TYPICAL OUTPUT CHARACTERISTICS



TYPICAL TRANSFER CHARACTERISTICS



DC CURRENT TRANSFER RATIO VS. COLLECTOR CURRENT



COLLECTOR TO EMITTER SATURATION VOLTAGE VS. COLLECTOR CURRENT

